# EAST Search History

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|---|---|---|---|---|---|---|
| S129 | 26 | (kirimura near2 hiroya or kiyoshi near2 ogata).in. and laser near10 crystal$7 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/02 19:16 |
| L2 | 17 | 1 and "without" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/02 19:16 |
| L1 | 26 | (kirimura near2 hiroya or kiyoshi near2 ogata).in. and laser near10 crystal$7 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/02 19:16 |
| L5 | 2 | 1 and "without" near4 dehydrogenation | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/02 19:18 |
| L3 | 2 | 1 and "without" near4 hydrogen | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/02 19:18 |
| L7 | 472 | laser near10 crystal$6 and ion near5 beam near10 deposit$5 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/02 19:20 |
| L6 | 1593 | laser near10 crystal$6 and ion near10 deposit$5 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/02 19:20 |
| L4 | 41280 | laser near10 crystal$6 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/02 19:20 |
| S15 | 83 | laser same anneal$3 same (silicon or si) and "117"/$4.ccls. and (CVD or chemical adj vapor adj deposition) same plasma | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/02 19:21 |

| L9 | 24 | laser near10 crystal$6 and ion near5 beam near10 deposit$5 near10 (si or silicon) and @py<"2002" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/02 19:21 |
|----|----|----|----|----|----|----|
| L8 | 191 | laser near10 crystal$6 and ion near5 beam near10 deposit$5 and @py<"2002" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/02 19:21 |
| L10 | 127 | laser same anneal$3 same (silicon or si) and "117"/$4.ccls. and (CVD or chemical adj vapor adj deposition) same plasma | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/02 19:33 |
| S61 | 165 | without near4 hydrogen near15 (si or silicon) near2 (layer film) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/02 19:34 |
| S17 | 78 | laser same anneal$3 same (silicon or si) and "117"/$4.ccls. and (CVD or chemical adj vapor adj deposition) same plasma same (si or silicon) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/02 19:34 |
| L12 | 200 | without near4 hydrogen near15 (si or silicon) near2 (layer film) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/02 19:34 |
| L11 | 120 | laser same anneal$3 same (silicon or si) and "117"/$4.ccls. and (CVD or chemical adj vapor adj deposition) same plasma same (si or silicon) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/02 19:34 |